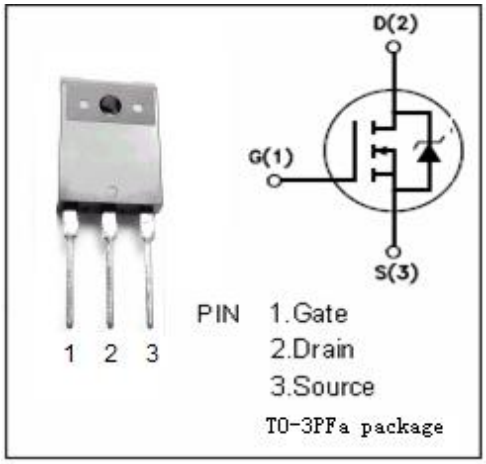
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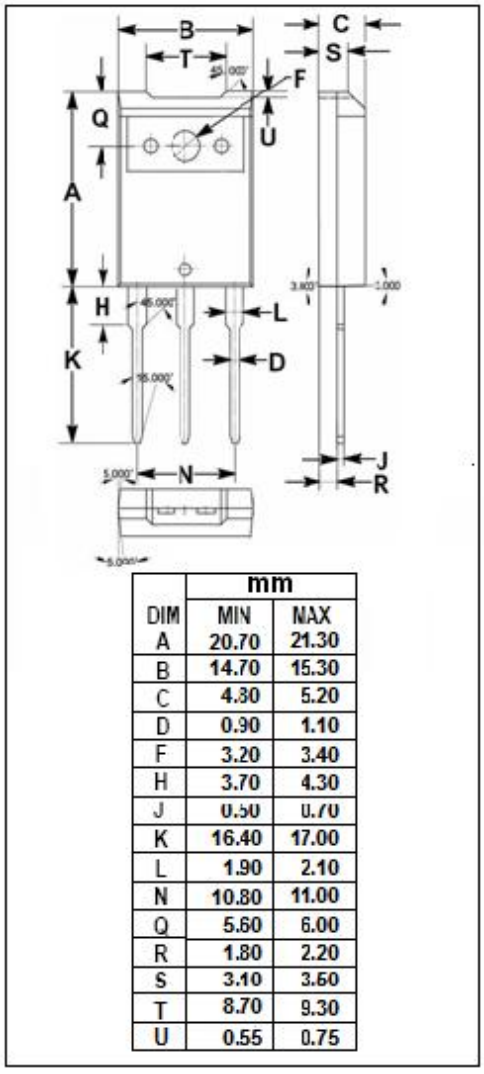


FEATURES

- Drain Current $-I_D$=3A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 400V(Min)

DESCRIPTION

- High Voltage.
- High speed power switching.



DIM	mm MIN	MAX
A	20.70	21.30
B	14.70	15.30
C	4.30	5.20
D	0.90	1.10
F	3.20	3.40
H	3.70	4.30
J	0.50	0.70
K	16.40	17.00
L	1.90	2.10
N	10.80	11.00
Q	5.60	6.00
R	1.80	2.20
S	3.10	3.60
T	8.70	9.30
U	0.55	0.75

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	400	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	3	A
P_D	Total Dissipation @T_C=25℃	80	W
T_J	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 0.25mA	400			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 1mA	1.0		5.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 2A			3.0	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 400V; V_{GS}=0			1	μA
V_{SD}	Forward On-Voltage	I_S= 3A; V_{GS}=0			1.3	V
tr	Rise time	VGS=10V;ID=3A; RL=50Ω		60	90	ns
ton	Turn-on time			80	120	ns
tf	Fall time			50	90	ns
toff	Turn-off time			130	175	ns

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